

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-10 (cancelled)

11. (currently amended) A semiconductor device comprising:

| a first circuit section formed to be including a first transistor which has a current passage between the first potential and the second potential included;

| a second circuit section formed to be including a second transistor which has a current passage between the third potential and the fourth potential;

a first pad that supplies the first potential to the first circuit section;

a second pad that supplies the second potential to the first circuit section;

a third pad that supplies the third potential to the second circuit section;

a fourth pad that supplies the fourth potential to the second circuit section;

a first bus-bar arranged along the direction where the first pad and the second pad are arranged, arranged between a plurality of inner leads and the first and second pads, connected to the first pad by a wire, and supplied with the first potential;

a second bus-bar arranged along the direction where the first pad and the second pad are arranged, arranged between a plurality of inner leads and the first and second pads, connected to the second pad by a wire, and supplied with the second potential;

a third bus-bar arranged along the direction where the third pad and the fourth pad are arranged, arranged between a plurality of inner leads and the third and fourth pads, connected to the third pad by a wire, and supplied with the third potential; and

a fourth bus-bar arranged along the direction where the third pad and the fourth pad are arranged, arranged between a plurality of inner leads and the third and fourth pads, connected to the fourth pad by a wire, and supplied with the fourth potential.

12. (original) The semiconductor device according to claim 11, wherein the first bus-bar has the first inner lead section supplied with the first potential and the third bus-

bar has the third inner lead section supplied with the third potential.

13. (original) The semiconductor device according to claim 12, wherein the second bus-bar has the second inner lead section supplied with the second potential and the fourth bus-bar has fourth inner lead section supplied with the fourth potential.

14. (original) The semiconductor device according to claim 12, wherein the second bus-bar is connected to the inner lead by a wire, to which the second potential is supplied, and the fourth bus-bar is connected to the inner lead by a wire, to which the fourth potential is supplied.

15. (original) The semiconductor device according to claim 11 further comprising:

a fifth pad for supplying a fifth potential to the first circuit section; and

a fifth bus-bar arranged along the direction where the first pad, the second pad, and the fifth pad are arranged, arranged between a plurality of inner leads and the fifth pad, connected to the fifth pad by a wire, and supplied with the fifth potential.

16. (original) The semiconductor device according to claim 15 further comprising:

a sixth pad for supplying a sixth potential to the second circuit section; and

a sixth bus-bar arranged along the direction where the third pad, the fourth pad, and the sixth pad are arranged, arranged between a plurality of inner leads and the sixth pad, connected to the sixth pad by a wire, and supplied with the sixth potential.

17. (original) The semiconductor device according to claim 16, wherein the fifth bus-bar is connected to the inner lead by a wire, to which the fifth potential is supplied, and the sixth bus-bar is connected to the inner lead by a wire, to which the sixth potential is supplied.

18. (original) The semiconductor device according to claim 11, wherein the first circuit section is a digital circuit and the second circuit section is an analog circuit.

19. (original) The semiconductor device according to claim 11, comprising a plurality of the first and the fourth pads.

20. (original) The semiconductor device according to claim 11 wherein the semiconductor chip that contain the first and the second circuit sections and the first to fourth pads, the plurality of inner leads, the first to the fourth bus-bars, and the wire are encapsulated by resin.

21. (original) The semiconductor device according to claim 11 wherein the second circuit section is arranged much more away from the first and the second bus-bars than the first circuit section and the third pad is contained in the second circuit section.

22. (original) The semiconductor device according to claim 11 wherein the second circuit section is connected to the third pad by a wire, contains the fifth pad that supplies the third potential to the second circuit section, and is arranged much more away from the first and the second bus-bars than the first circuit section.

Claims 23-51 (cancelled)